

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1-44. (cancelled)

45. (currently amended) A process for producing a semiconductor device, comprising consisting essentially of:

providing a wafer for forming an integrated circuit thereon, the wafer having a main surface on which an integrated circuit is to be formed, a substantially circular contour portion surrounding said main surface, a curved positioning notch formed in said circular contour portion and connecting portions defined between said circular contour portion and said curved positioning notch;

wherein an outer peripheral part of said wafer is chamfered in a thickness direction by mechanical chamfering, and

wherein said connecting portions are chamfered in a plane parallel to said main surface by mechanical chamfering.

46. (currently amended) A process for producing a semiconductor device, comprising consisting essentially of:

providing wafer for forming an integrated circuit thereon, the wafer having a main surface on which an integrated circuit is to be formed, a substantially circular contour portion surrounding said main surface, a curved

positioning notch formed in said circular contour portion and connecting portions defined between said circular contour portion and said curved positioning notch;

_____ wherein an outer peripheral part of said wafer is chamfered in a thickness direction by grindstone, and

_____ wherein said connecting portions are chamfered in a plane parallel to said main surface by grindstone.

47. (currently amended) A process for producing a semiconductor device, comprising consisting essentially of:

_____ providing a wafer for forming an integrated circuit thereon, the wafer having a main surface on which an integrated circuit is to be formed, a substantially circular contour portion surrounding said main surface, a curved positioning notch formed in said circular contour portion and connecting portions defined between said circular portion and said curved positioning notch, wherein said connecting portions are chamfered in a plane parallel to said main surface; and

_____ positioning said wafer by rotating said wafer.

48. (previously presented) A process for producing a semiconductor device according to claim 47, wherein, in the positioning step, positioning said wafer by using photoelectric elements.

49. (previously presented) A process for producing a semiconductor device according to claim 48, wherein an outer peripheral part

of said wafer is chamfered in a thickness direction by mechanical chamfering,
and

_____ wherein said connecting portions are chamfered in a plane parallel to
said main surface by mechanical chamfering.

50. (previously presented) A process for producing a
semiconductor device according to claim 48, wherein an outer peripheral part
of said wafer is chamfered in a thickness direction by grindstone, and
_____ wherein said connecting portions are chamfered in a plane parallel to
said main surface by grindstone.

51. (previously presented) A process for producing a
semiconductor device according to claim 47, wherein, in the positioning step,
positioning said wafer by optical means.

52. (previously presented) A process for producing a
semiconductor device according to claim 47, wherein an outer peripheral part
of said wafer is chamfered in a thickness direction by mechanical chamfering,
and
_____ wherein said connecting portions are chamfered in a plane parallel to
said main surface by mechanical chamfering.

53. (previously presented) A process for producing a
semiconductor device according to claim 47, wherein an outer peripheral part
of said wafer is chamfered in a thickness direction by grindstone, and

wherein said connecting portions are chamfered in a plane parallel to
said main surface by grindstone.

54-60. (cancelled)